

Inventor(s): MIYASHITA et al.

Appln. No.: 09 916,530

Series Code ↑

Serial No. ↑

Filed: July 30, 2001

Hon. Commissioner of Patents
Washington, D.C. 20231

Sir:

REPLY/AMENDMENT/LETTER

Group Art Unit

2812

Examiner:

Ron Everett Pompey

Atty. Dkt.

P

279038

T1HM-98S0740-D

M#

Client Ref

Appln. Title: Semiconductor device comprising metal silicide films formed to cover gate electrode and source-drain diffusion layers and method of manufacturing the same

Date: February 20, 2003

This is a reply/amendment/letter in the above-identified application and includes the herewith attachment of same date and subject which is incorporated hereinto by reference and the signature below is treated as the signature to the attachment in absence of a signature thereto.

FEE REQUIREMENTS FOR CLAIMS AS AMENDED

1. Small Entity claim

- A. ☒ NOT made
B. ☐ Withdrawn
C. ☐ made herewith
D. ☐ made previously

For B & C
See **Required**
Separate Paper
(Pat-256)

	Claims remaining after amendment	Highest number previously paid for	Present Extra	Large/Small Entity	Additional Fee	Fee Code Lg/Sm
2. Total Effective Claims	2	**minus 20	0	x \$18/\$9 =	+ \$0	103/203
3. Independent Claims	1	***minus 3	0	x \$84/\$42 =	+ \$0	102/202
4. If amendment enters proper multiple dependent claim(s) into this application for first time (leave blank if this is a reissue application) add				+ \$280/\$140 =	+ \$0	104/204
5. Original due Date: February 20, 2003	<input type="checkbox"/> NONE					
6. Petition is hereby made to extend the original due date to cover the date this response is filed for which the requisite fee is attached	(1 mo)	\$110/\$55 =		+ \$0		115/215
	(2 mos)	\$400/\$200 =				116/216
	(3 mos)	\$920/\$460 =				117/217
	(4 mos)	\$1,440/\$720 =				118/218
	(5 mos)	\$1,960/\$980 =				128/228
7. Enter any previous extension fee paid since above original due date and subtract				- \$0		
8.	Extension Fee				+ \$0	
9. If Terminal Disclaimer attached, add Rule 20(d) official fee				+ \$110/\$55	+ \$0	148/248
10. If IDS attached requires Official Fee under Rule 97 (c), add				+ \$180	+ \$0	126
or if Rule 97(d) Request add				+ \$180		126
11. After-Final Request Fee per rules 129(a) and 17(r)				+ \$740/370	+ \$0	146/246
12. No. of additional inventions for examination per Rule 129(b).....				x \$740/370 ea	+ \$0	149/249
13. Request for Continued Examination (RCE)				+ \$740/370	+ \$0	1179/1279
14. Petition fee for					+ \$0	
15.	TOTAL FEE =				\$0	
16. *If the entry in this space is less than entry in next space, the "Present Extra" result is "0".						PLEASE CHARGE OUR DEP. ACCT
17. **If the "Highest number previously paid for" in this space is less than 20, write "20" in this space.						
18. ***If the "Highest number previously paid for" in this space is less than 3, write "3" in this space.						

Our Deposit Account No. 03-3975)

(Our Order No. 8312 279038

C#

M#

CHARGE STATEMENT: The Commissioner is hereby authorized to charge any fee specifically authorized hereafter, or any missing or insufficient fee(s) filed, or asserted to be filed, or which should have been filed herewith or concerning any paper filed hereafter, and which may be required under Rules 16-18 (missing or insufficiencies only) now or hereafter relative to this application and the resulting Official Document under Rule 20, or credit any overpayment, to our Accounting/Order Nos. shown above, for which purpose a duplicate copy of this sheet is attached.

This CHARGE STATEMENT does not authorize charge of the issue fee until/unless an issue fee transmittal sheet is filed.

Query: Is appeal deadline now? If so, file Notice of Appeals separately.

Pillsbury Winthrop LLP
Intellectual Property Group

By Atty: Glenn J. Perry

Sig: *GP* 39328

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Atty/Sec: gjp/ml

NOTE: File this cover sheet in duplicate with PTO receipt (PAT-103A) and attachments



10/B
3/3/03
Mmi=h

In re PATENT APPLICATION OF
MIYASHITA et al.

Confirmation No.: 9248

Group Art Unit: 2812

Appln. No.: 09/916,530

Examiner: Ron Everett Pompey

Filed: July 30, 2001

Title: Semiconductor device comprising metal silicide films formed to cover gate electrode and source-drain diffusion layers and method of manufacturing the same

February 20, 2003

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RESPONSE TO OFFICE ACTION

Hon. Commissioner of Patents
Washington, D.C. 20231

Sir:

In response to the Official Action dated November 20, 2002, please amend this application as set forth herein. This Amendment is intended to comply with the new format promulgated by the USPTO in February, 2003. ✓

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FEB 24 2003
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